NSN 5961-01-297-8605

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View Online at https://aerobasegroup.com/nsn/5961-01-297-8605 **Inclosure Material:** Metal **Overall Length:** 1.550 inches **Overall Height:** 0.330 inches **Overall Width:** 1.550 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: -120.0 collector to base voltage, dc and -120.0 collector to emitter voltage, dc and -5.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** -100.00 amperes source cutoff current and -2.00 amperes source cutoff current **Power Rating Per Characteristic:** 300.0 watts small-signal input power, common-collector absolute **Transfer Ratio:** 3.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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